This GIDEP PCN is to announce specifications change with the datasheet parameters for the following International Rectifier Part No. Note that this change is related to part specification only, and not due to a die physical change.

IRHNJ67230 [2N7591U3]
200V, N-Channel TID Hardened MOSFET in a SMD-0.5 package.

**ELECTRICAL CHARACTERISTICS @ Tj = 25°C**

- \( Q_g \) [Total Gate Charge], change max limit from 42nC to 50nC.
- \( Q_{gd} \) [Gate-to-Drain (‘Miller’) Charge], change max limit from 15nC to 20nC.
- \( t_{d(on)} \) [Turn-On Delay Time], change max limit from 18ns to 25ns.
- \( t_r \) [Rise Time], change max limit from 32ns to 30ns.
- \( t_{d(off)} \) [Turn-Off Delay Time], change max limit from 41ns to 60ns.
- \( t_f \) [Fall Time], change max limit from 10ns to 30ns.

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

- \( t_{rr} \) [Reverse Recovery Time], change max limit from 346ns to 350ns.

Reference Datasheet PD-96923